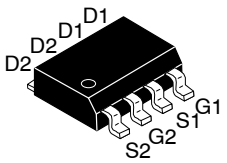
MOSFET – Dual, N-Channel, POWERTRENCH®

2.5 V Specified

FDS9926A



SOIC8
CASE 751EB

General Description

These N−Channel 2.5 V specified MOSFETs use **onsemi**'s advanced POWERTRENCH process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5 V – 10 V).

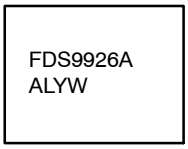
Features

- 6.5 A, 20 V. $R_{DS(ON)}$ = 30 mΩ @ V_{GS} = 4.5 V
  $R_{DS(ON)}$ = 43 mΩ @ V_{GS} = 2.5 V
- Optimized for Use in Battery Protection Circuits
- Low Gate Charge
- This Device is Pb−Free and Halide Free

Applications

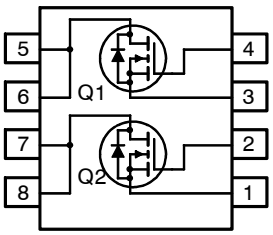
- Battery Protection
- Load Switch
- Power Management

MARKING DIAGRAM



FDS9926A	= Specific Device Code
A	= Assembly Site
L	= Wafer Lot Number
YW	= Assembly Start Week

ELECTRICAL CONNECTION



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain−Source Voltage		20	V
V_{GSS}	Gate−Source Voltage		±10	V
I_D	Drain Current	Continuous (Note 1a)	6.5	A
		Pulsed	20	
P_D	Power Dissipation	for Dual Operation	2	W
		for Single Operation (Note 1a) (Note 1b) (Note 1c)	 1.6 1 0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	40	°C/W

ORDERING INFORMATION

Device	Package	Shipping†
FDS9926A	SOIC8	2500 / Tape & Reel

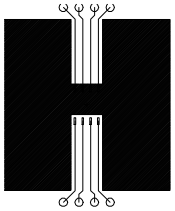
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

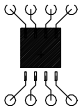
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	20	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	–	14	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16 V, V_{GS} = 0 V	–	–	1	μA
I_{GSS}	Gate–Body Leakage	V_{GS} = ±8 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	0.6	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	–	–3	–	mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 4.5 V, I_D = 6.5 A	–	25	30	mΩ
		V_{GS} = 2.5 V, I_D = 5.4 A	–	35	43	
		V_{GS} = 4.5 V, I_D = 6.5 A, T_J = 125°C	–	35	50	
$I_{D(on)}$	On–State Drain Current	V_{GS} = 4.5 V, V_{DS} = 5 A	15	–	–	A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 6.5 A	–	22	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz	–	650	–	pF
C_{oss}	Output Capacitance		–	150	–	pF
C_{rss}	Reverse Transfer Capacitance		–	85	–	pF
R_G	Gate Resistance	V_{GS} = 15 mV, f = 1.0 MHz	–	1.4	–	Ω
SWITCHING CHARACTERISTICS (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 10 V, I_D = 1 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω	–	8	16	ns
t_r	Turn–On Rise Time		–	9	17	ns
$t_{d(off)}$	Turn–Off Delay Time		–	15	26	ns
t_f	Turn–Off Fall Time		–	4	9	ns
Q_g	Total Gate Charge	V_{DS} = 10 V, I_D = 3 A, V_{GS} = 4.5 V	–	6.2	9	nC
Q_{gs}	Gate–Source Charge		–	1.2	–	nC
Q_{gd}	Gate–Drain Charge		–	1.7	–	nC
DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.3 A (Note 2)	–	0.73	1.3	V
t_{rr}	Diode Reverse Recovery Time	I_F = 6.5 A, d_{iF}/d_t = 100 A/μs	–	15	–	ns
Q_{rr}	Diode Reverse Recovery Charge		–	5	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

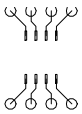
1. $R_{\theta JA}$ is the sum of the junction–to–case and case–to–ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while RqCA is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in^2 pad of 2 oz. Copper



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper



c) 135°C/W when mounted on a minimum pad.

2. Pulse Test Pulse Width < 300 μs, Duty Cycle < 2.0%

TYPICAL CHARACTERISTICS

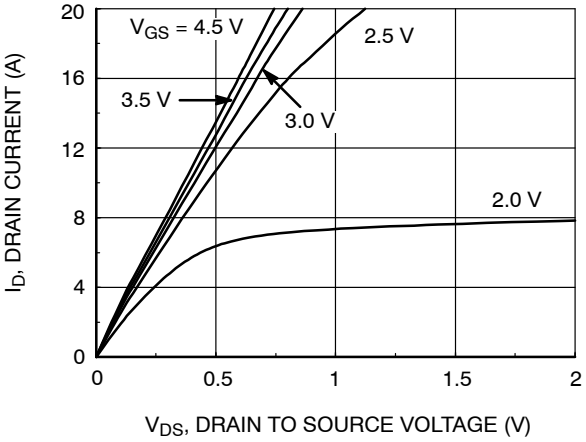


Figure 1. On−Region Characteristics

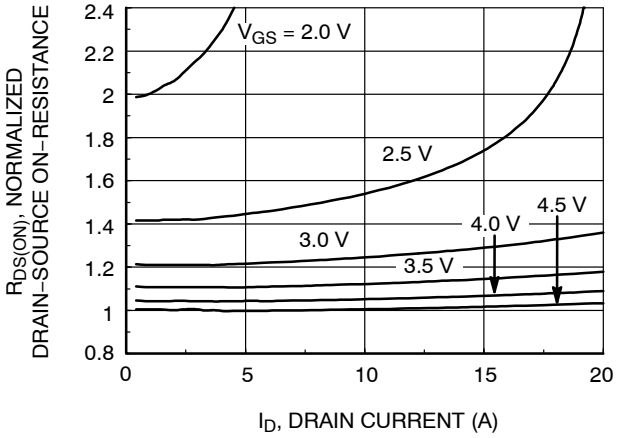


Figure 2. On−Resistance Variation with Drain Current and Gate Voltage

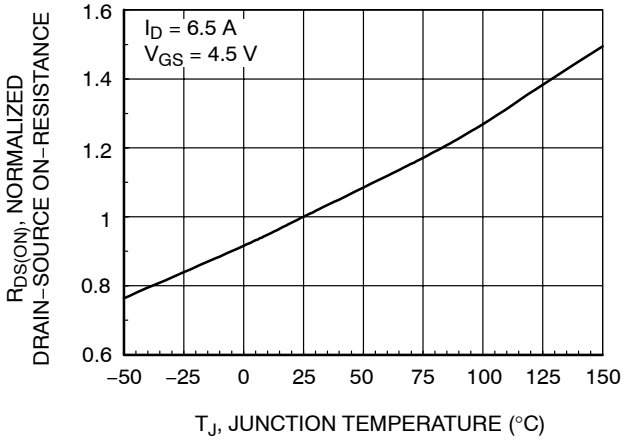


Figure 3. On−Resistance Variation with Temperature

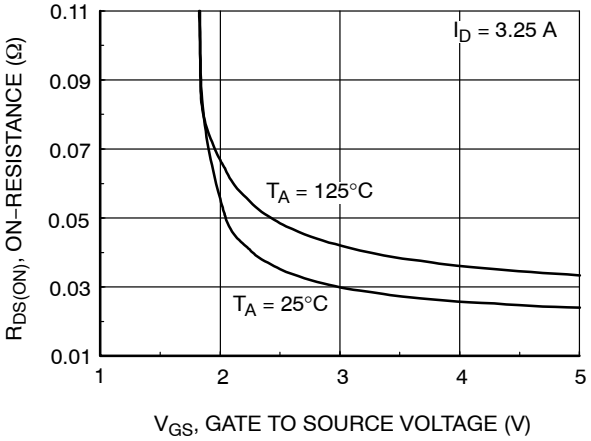


Figure 4. On−Resistance Variation with Gate−to−Source Voltage

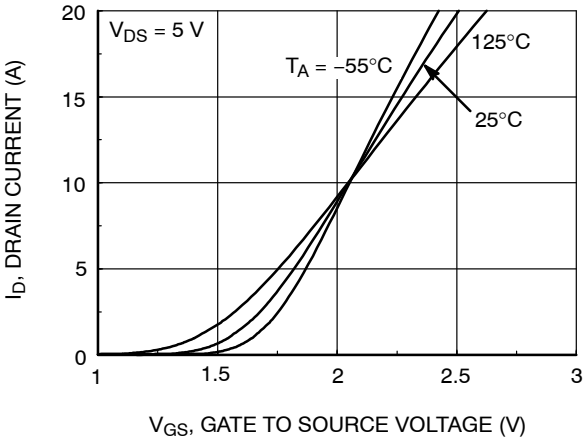


Figure 5. Transfer Characteristics

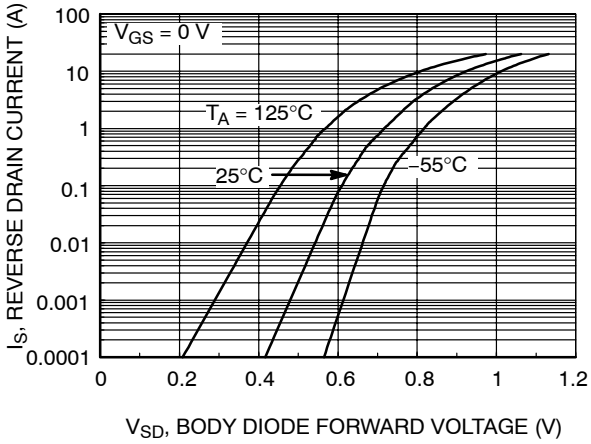


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL CHARACTERISTICS (continued)

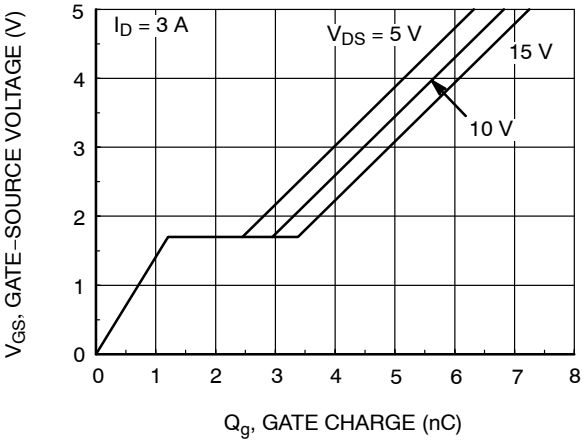


Figure 7. Gate−Charge Characteristics

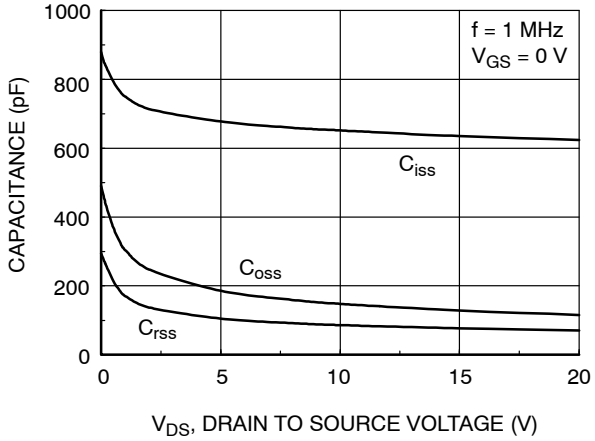


Figure 8. Capacitance Characteristics

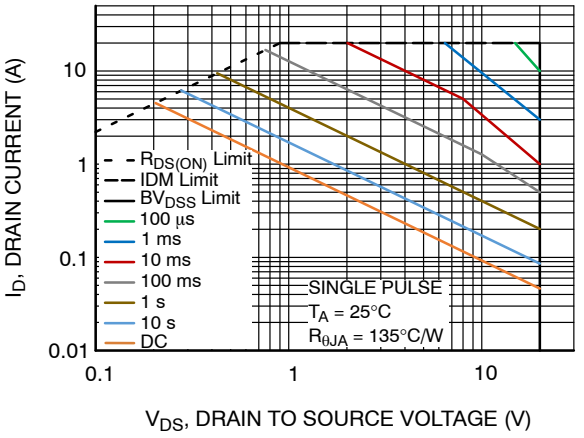


Figure 9. Maximum Safe Operating Area

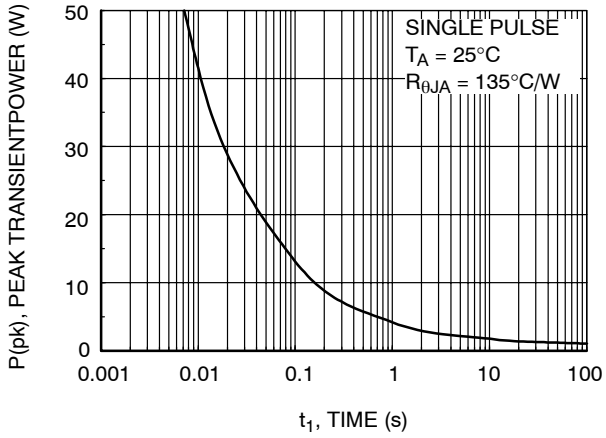


Figure 10. Single Pulse Maximum Power Dissipation

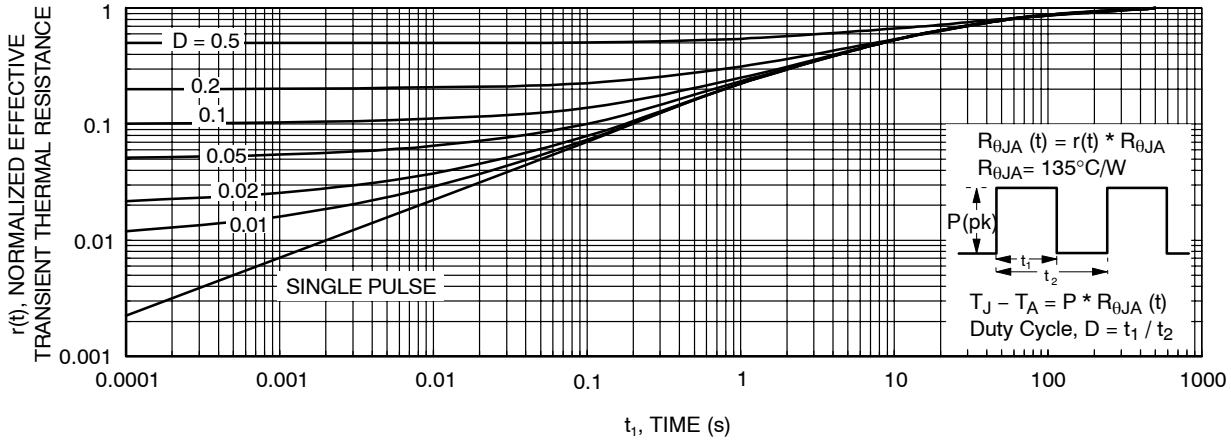


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1c.
Transient themal response will change depending on the circuit board design.

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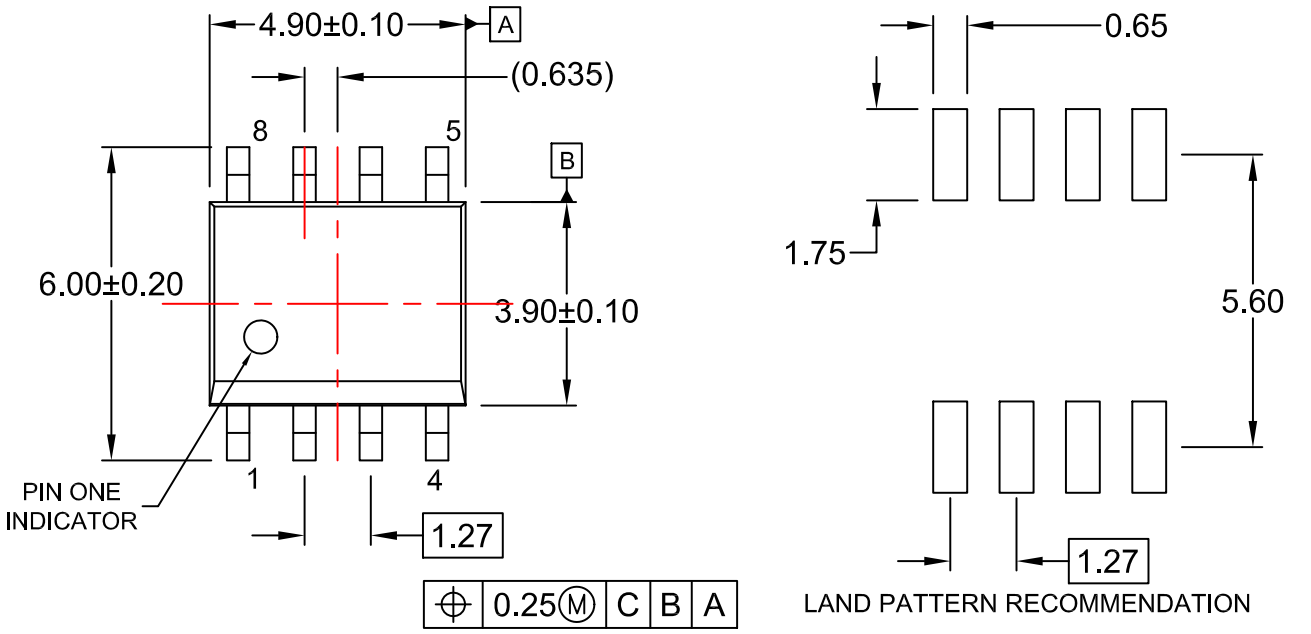
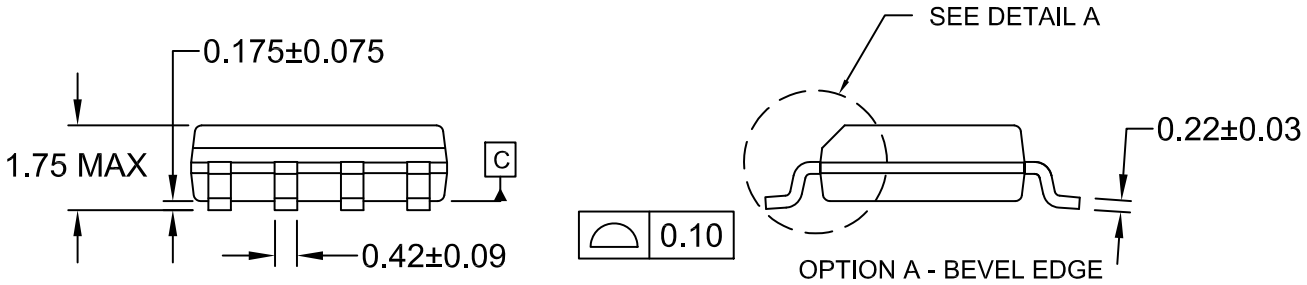
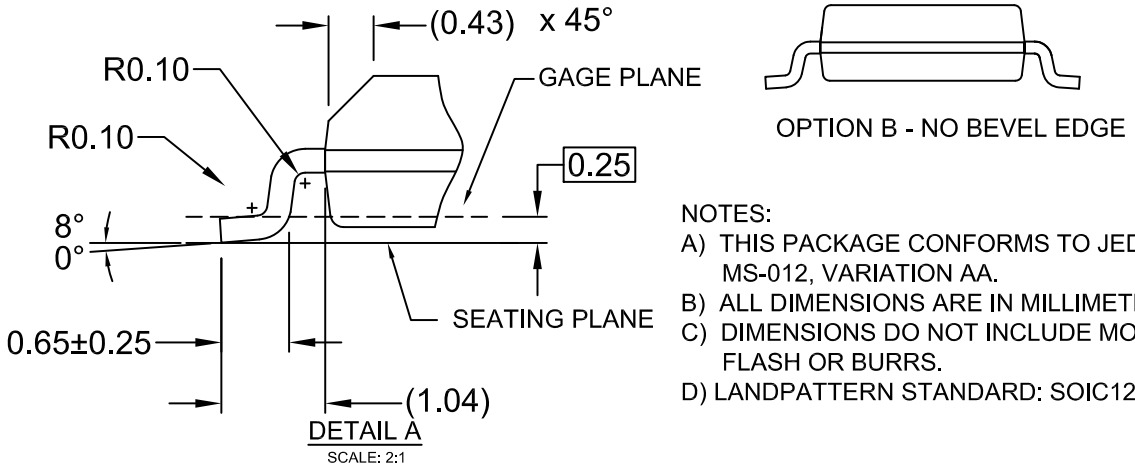
ISSUE A

DATE 24 AUG 2017







NOTES:
A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M

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